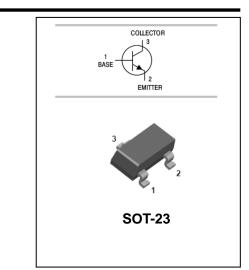
BL Galaxy Electrical

Silicon Epitaxial Planar Transistor

S9014

FEATURES

- Complementary To S9015.
- Excellent H_{FE} Linearity.
- Power dissipation.(P_C=0.2W)



APPLICATIONS

Per-Amplifier low level & low noise.

ORDERING INFORMATION

Type No.	Marking	Package Code	
S9014	J6	SOT-23	

Lead-free

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	100	mA
P _C	Collector Dissipation	200	mW
$T_{j,T_{stg}}$	Junction and Storage Temperature	-55~150	$^{\circ}$

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Rev.A



Silicon Epitaxial Planar Transistor

S9014

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μΑ,I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =0.1mA,I _B =0	45			>
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μΑ,I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =50V,I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =35V,I _B =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =3V,I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =5V,I _C =1mA	200		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B = 5mA			0.3	\
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B = 5mA			1	V
Transition frequency	f⊤	V_{CE} =6V, I_{C} = 20mA f=30MHz		150		MHz

CLASSIFICATION OF $h_{\text{FE}(1)}$

Rank	L	Н
Range	200-450	450-1000

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Silicon Epitaxial Planar Transistor

S9014

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

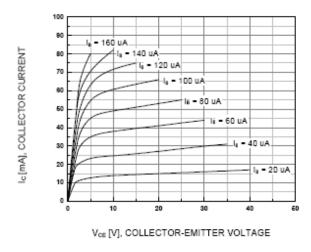


Figure 1. Static Characteristic

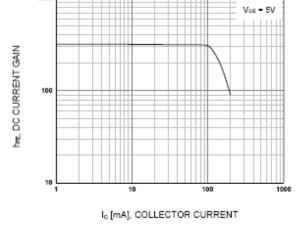


Figure 2. DC current Gain

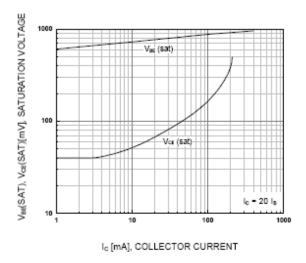


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

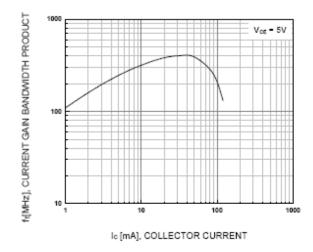


Figure 4. Current Gain Bandwidth Product

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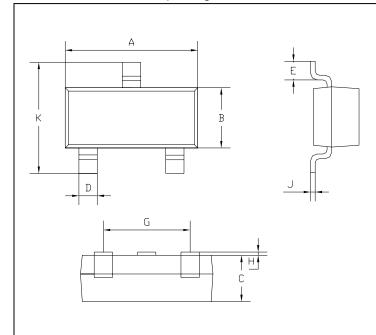
Silicon Epitaxial Planar Transistor

S9014

PACKAGE OUTLINE

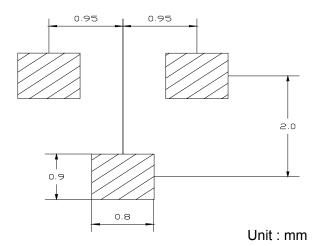
Plastic surface mounted package

SOT-23



SOT-23			
Dim	Min	Max	
Α	2.85	2.95	
В	1.25	1.35	
С	1.0Typical		
D	0.37	0.43	
Е	0.35	0.48	
G	1.85	1.95	
Н	0.02	0.1	
J	0.1Typical		
K	2.35	2.45	
All Dimensions in mm			

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
S9014	SOT-23	3000/Tape&Reel